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Vishay Siliconix

# Automotive N-Channel 55 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	55				
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS}$ = 10 V	0.020				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.026				
I <sub>D</sub> (A)	30				
Configuration	Single				
Package	TO-252				

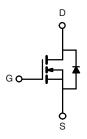
Top View

# TO-252 To-252 Drain connected to tab

#### **FEATURES**

- TrenchFET® power MOSFET
- 100 % R<sub>g</sub> and UIS tested
- AEC-Q101 qualified d
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





N-Channel MOSFET

PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V <sub>DS</sub>	55	M	
Gate-Source Voltage		$V_{GS}$	± 20	V	
Continuous Drain Current	T <sub>C</sub> = 25 °C <sup>a</sup>	l <sub>D</sub>	30		
Continuous Drain Current	T <sub>C</sub> = 125 °C		19		
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	30	Α	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	120		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	20		
Single Pulse Avalanche Energy	L = U.T IIII	E <sub>AS</sub>	20	mJ	
Maximum Power Dissipation b	T <sub>C</sub> = 25 °C	T <sub>C</sub> = 25 °C		W	
Maximum Fower Dissipation 5	T <sub>C</sub> = 125 °C	$P_{D}$	16	, v	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stq</sub>	-55 to +175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount <sup>c</sup>	$R_{thJA}$	60	°C/W	
Junction-to-Case (Drain)		$R_{thJC}$	3	C/ VV	

## Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		55	-	-	.,,
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		2	2.5	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 55 V	-	-	1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 55 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 55 V, T <sub>J</sub> = 175 °C	-	-	250	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{GS} = 5 V$	$V_{DS} \ge 5 V$	30	-	-	Α
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A	-	0.016	0.020	Ω
Due in Course On Chata Basistana 3	D.	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C	-	-	0.035	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 175 °C	-	-	0.043	
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 15 A	-	0.021	0.026	
Forward Transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A		-	34	-	S
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			=	938	1175	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 25 V, f = 1 MHz	-	203	255	pF
Reverse Transfer Capacitance	C <sub>rss</sub>	1		-	86	110	
Total Gate Charge <sup>c</sup>	Qg			=	12	18	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{GS} = 5 V$	$V_{DS} = 25 \text{ V}, I_D = 35 \text{ A}$	-	4.1	-	nC
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>	1		-	4.8	-	
Gate Resistance	R <sub>g</sub>	f = 1 MHz		1	2.1	4.5	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>				7	11	- ns
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = 25 V, $R_L$ = 0.71 Ω $I_D$ $\cong$ 35 A, $V_{GEN}$ = 10 V, $R_g$ = 1 Ω		-	10	15	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	18	27	
Fall Time <sup>c</sup>	t <sub>f</sub>			-	5	8	
Source-Drain Diode Ratings and Chara	acteristics b						•
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	120	Α
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = 80 A, V <sub>GS</sub> = 0 V			1.2	1.5	V

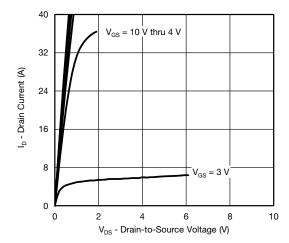
#### **Notes**

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

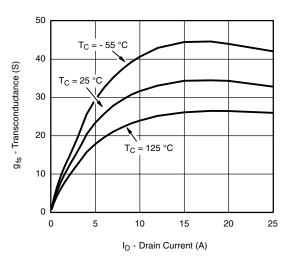
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



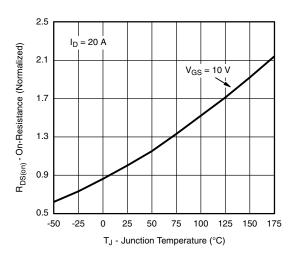
# **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



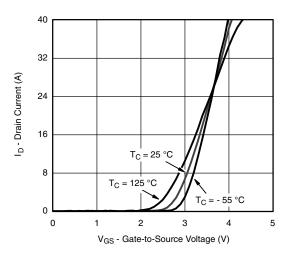
#### **Output Characteristics**



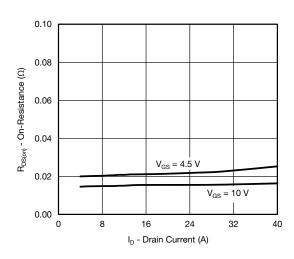
# Transconductance



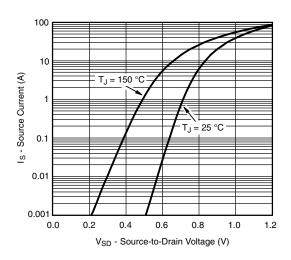
On-Resistance vs. Junction Temperature



#### **Transfer Characteristics**



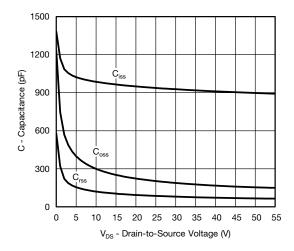
### **On-Resistance vs. Drain Current**

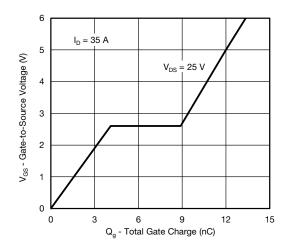


**Source Drain Diode Forward Voltage** 

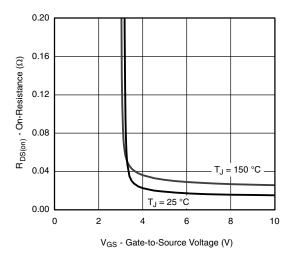


# **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

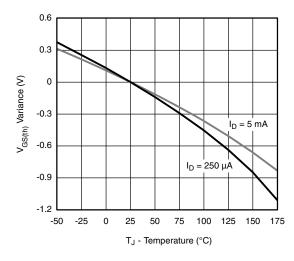




#### Capacitance

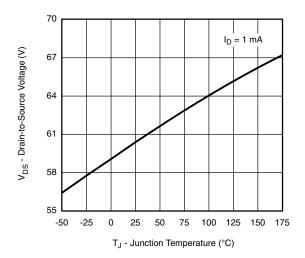


**Gate Charge** 



## On-Resistance vs. Gate-to-Source Voltage



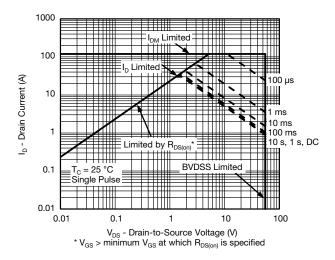


Drain Source Breakdown vs. Junction Temperature

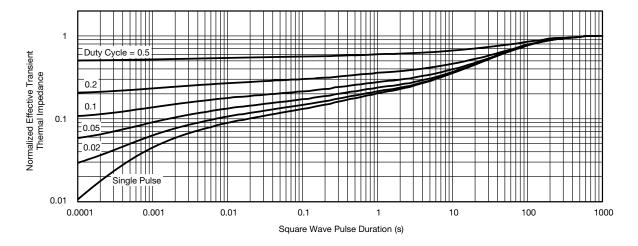
For technical questions, contact: automostech



# **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



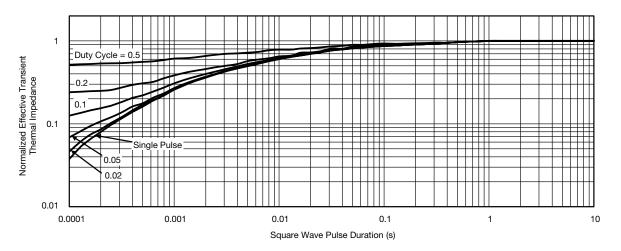
#### Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



# THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg267054">www.vishay.com/ppg267054</a>.



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REVISION	HISTORY a	
REVISION	DATE	DESCRIPTION OF CHANGE
D	04-Aug-15	Revised R <sub>g</sub> minimum limit

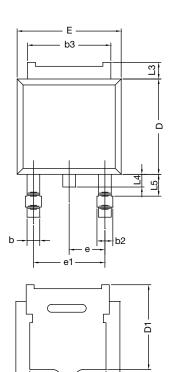
#### Note

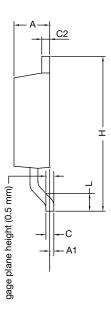
a. As of April 2014



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# **TO-252AA Case Outline**





	MILLIN	METERS	INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090	BSC	
e1	4.56	BSC	0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T13-0592-Rev. A, 02-Sep-13					

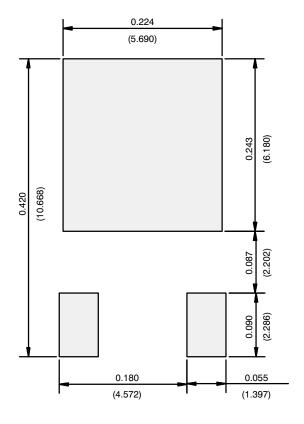
## DWG: 6019

Note

• Dimension L3 is for reference only.



# **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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